L Number	Hits	Search Text	DB	Time stamp
260	1259	semiconductor and ((dummy shield$3) near1 (pattern wire wiring layer)) and (power and (ground grounding))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 16:20
261	316	(semiconductor and ((dummy shield$3) near1 (pattern wire wiring layer)) and (power and (ground grounding))) and (silicon near1 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 16:20
262	69	((semiconductor and ((dummy shield$3) near1 (pattern wire wiring layer)) and (power and (ground grounding))) and (silicon near1 substrate)) and (dummy near1 (pattern wire wiring layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 16:22
263	2541	designing near device	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 16:23
264	260	(semiconductor and ((dummy shield$3) near1 (pattern wire wiring layer)) and (power and (ground grounding))) and (dummy near1 (pattern wire wiring layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 16:23
265	3	(designing near device) and ((semiconductor and ((dummy shield$3) near1 (pattern wire wiring layer)) and (power and (ground grounding))) and (dummy near1 (pattern wire wiring layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/17 16:23